

4M-WORD BY 64-BIT SYNCHRONOUS DYNAMIC RAM MODULE

UNBUFFERED TYPE

Description

The MC-454CB646 is a 4,194,304 words by 64 bits synchronous dynamic RAM module on which 4 pieces of 64M SDRAM : μ PD4564163 (Revision E) are assembled.

This module provides high density and large quantities of memory in a small space without utilizing the surface-mounting technology on the printed circuit board.

Decoupling capacitors are mounted on power supply line for noise reduction.

Features

- 4,194,304 words by 64 bits organization
- Clock frequency and clock access time

Family	/CAS latency	Clock frequency (MAX.)	Clock access time (MAX.)	Power consumption (MAX.)	
				Active	Standby
MC-454CB646-A80	CL = 3	125 MHz	6 ns	2,808 mW	7.2 mW (CMOS level input)
	CL = 2	100 MHz	6 ns	2,376 mW	
MC-454CB646-A10	CL = 3	100 MHz	6 ns	2,376 mW	
	CL = 2	77 MHz	7 ns	1,872 mW	

- Fully Synchronous Dynamic RAM, with all signals referenced to a positive clock edge
- Pulsed interface
- Possible to assert random column address in every cycle
- Quad internal banks controlled by BA0 and BA1 (Bank Select)
- Programmable burst-length : 1, 2, 4, 8 and full page
- Programmable wrap sequence (sequential / interleave)
- Programmable /CAS latency (2, 3)
- Automatic precharge and controlled precharge
- CBR (Auto) refresh and self refresh
- All DQs have $10\ \Omega \pm 10\%$ of series resistor
- Single $3.3\ \text{V} \pm 0.3\ \text{V}$ power supply
- LVTTTL compatible
- 4,096 refresh cycles / 64 ms
- Burst termination by Burst Stop command and Precharge command
- 168-pin dual in-line memory module (Pin pitch = 1.27 mm)
- Unbuffered type
- Serial PD

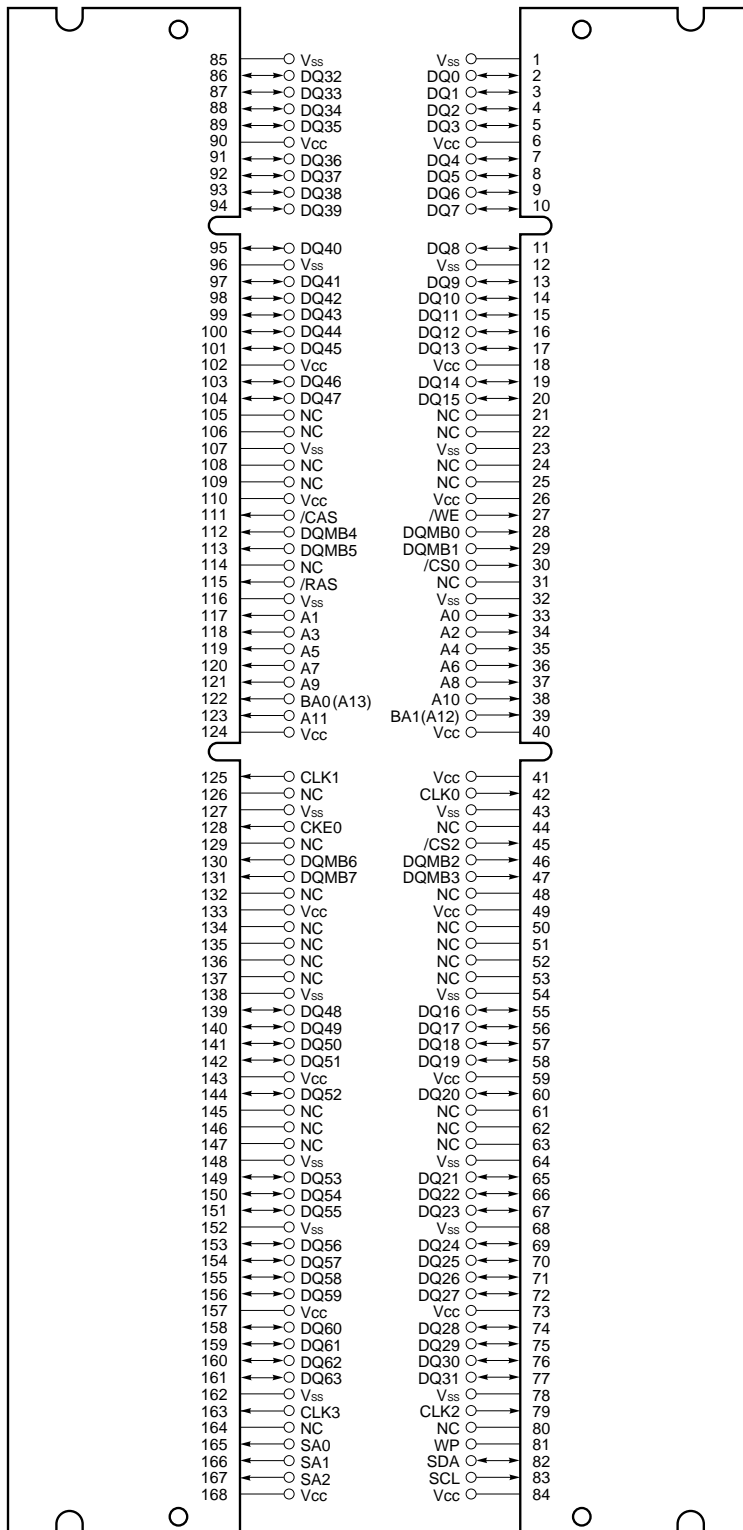
The information in this document is subject to change without notice.

Ordering Information

Part number	Clock frequency (MAX.)	Package	Mounted devices
MC-454CB646F-A80	125 MHz	168-pin Dual In-line Memory Module (Socket Type)	4 pieces of μ PD4564163G5 (Revision E) (400 mil TSOP (II))
MC-454CB646F-A10	100 MHz	Edge connector : Gold plated 34.93 mm (1.375 inch) height	[Single side]

Pin Configuration

168-pin Dual In-line Memory Module Socket Type (Edge connector: Gold plated)
 [MC-454CB646F]

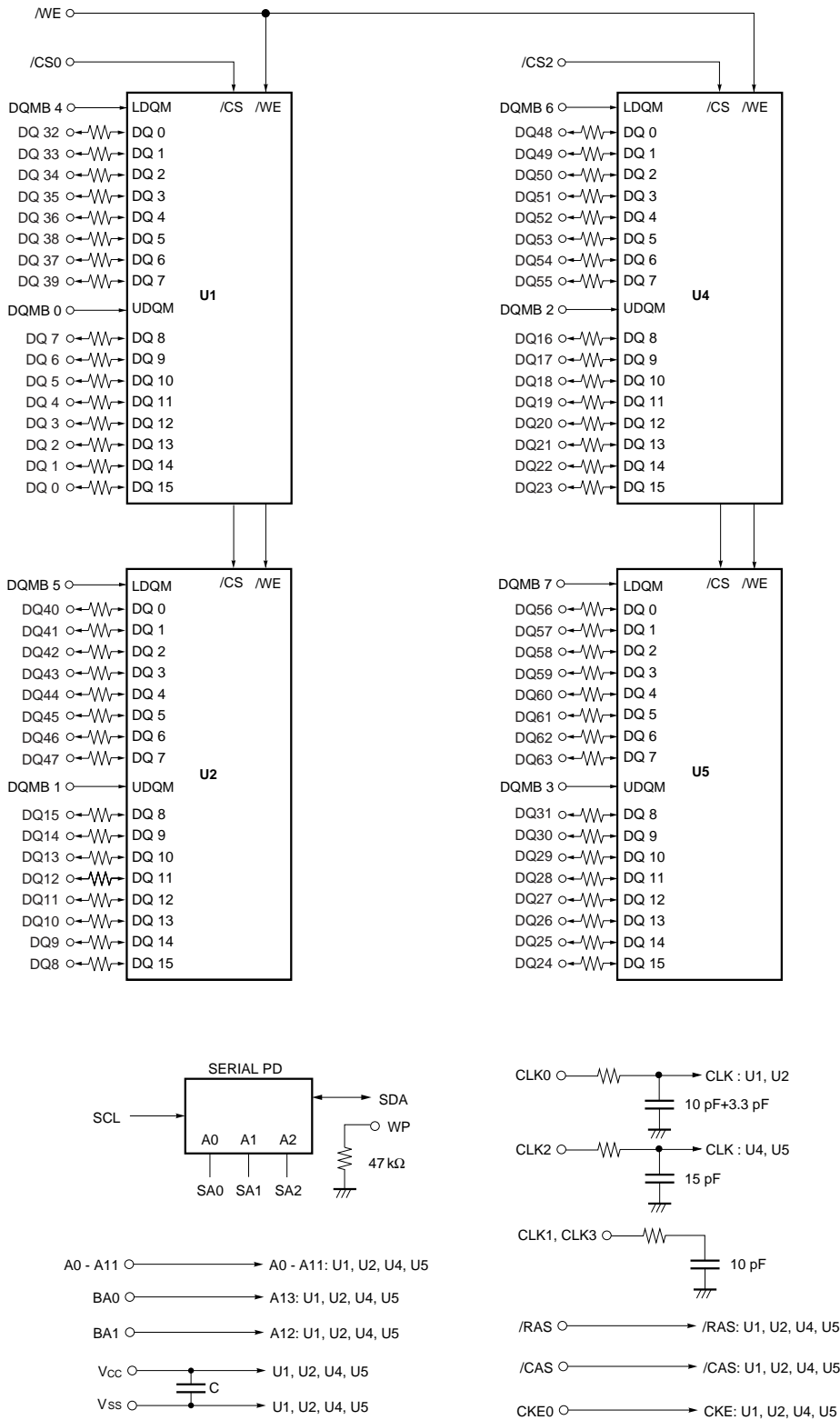


/XXX indicates active low signal.

- A0 - A11 : Address Inputs
 [Row : A0 - A11, Column : A0 - A7]
- BA0 (A13),
 BA1 (A12) : SDRAM Bank Select
- DQ0 - DQ63 : Data Inputs / Outputs
- CLK0, CLK1 : Clock Input
- CKE0 : Clock Enable Input
- WP : Write Protect ^{Note}
- /CS0, /CS2 : Chip Select Input
- /RAS : Row Address Strobe
- /CAS : Column Address Strobe
- /WE : Write Enable
- DQMB0 - DQMB7 : DQ Mask Enable
- SA0 - SA2 : Address Input for EEPROM
- SDA : Serial Data I/O for PD
- SCL : Clock Input for PD
- V_{cc} : Power Supply
- V_{ss} : Ground
- NC : No Connection

Note WP is not used yet. It is connected to ground.

★ Block Diagram



- Remarks**
1. The value of all resistors is 10 Ω except WP.
 2. WP is not used yet. It is connected to ground.
 3. U1, U2, U4, U5 : μPD4564163 (Revision E)(1M words × 16 bits × 4 banks)

Electrical Specifications

- All voltages are referenced to V_{SS} (GND).
- After power up, wait more than 100 μ s and then, execute power on sequence and auto refresh before proper device operation is achieved.

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Voltage on power supply pin relative to GND	V _{CC}		-0.5 to +4.6	V
Voltage on input pin relative to GND	V _T		-0.5 to +4.6	V
Short circuit output current	I _O		50	mA
Power dissipation	P _D		4	W
Operating ambient temperature	T _A		0 to +70	°C
Storage temperature	T _{sig}		-55 to +125	°C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{CC}		3.0	3.3	3.6	V
High level input voltage	V _{IH}		2.0		V _{CC} +0.3	V
Low level input voltage	V _{IL}		-0.3		+0.8	V
Operating ambient temperature	T _A		0		70	°C

★ **Capacitance (T_A = 25 °C, f = 1 MHz)**

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	C _{I1}	A0 - A11, BA0 (A13), BA1 (A12), /RAS, /CAS, /WE	22		40	pF
	C _{I2}	CLK0, CLK2	24		40	
	C _{I3}	CKE0	22		40	
	C _{I4}	/CS0, /CS2	12		20	
	C _{I5}	DQMB0 - DQMB7	7		13	
Data input / output capacitance	C _{I/O}	DQ0 - DQ63	7		13	pF

DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

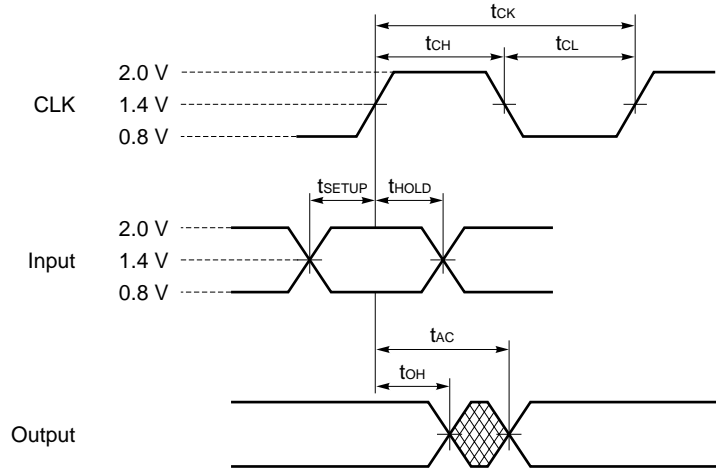
Parameter	Symbol	Test condition	Grade	MIN.	MAX.	Unit	Notes
★ ★ Operating current	I _{CC1}	Burst length = 1, t _{RC} ≥ t _{RC(MIN.)} , I _O = 0 mA	/CAS latency = 2	-A80	360	mA	1
				-A10	320		
			/CAS latency = 3	-A80	460		
				-A10	360		
Precharge standby current in power down mode	I _{CC2P}	CKE ≤ V _{IL(MAX.)} , t _{CK} = 15 ns			4	mA	
	I _{CC2PS}	CKE ≤ V _{IL(MAX.)} , t _{CK} = ∞			2		
Precharge standby current in non power down mode	I _{CC2N}	CKE ≥ V _{IH(MIN.)} , t _{CK} = 15 ns, /CS ≥ V _{IH(MIN.)} , Input signals are changed one time during 30 ns.			80	mA	
	I _{CC2NS}	CKE ≥ V _{IH(MIN.)} , t _{CK} = ∞, Input signals are stable.			24		
Active standby current in power down mode	I _{CC3P}	CKE ≤ V _{IL(MAX.)} , t _{CK} = 15 ns			20	mA	
	I _{CC3PS}	CKE ≤ V _{IL(MAX.)} , t _{CK} = ∞			16		
★ Active standby current in non power down mode	I _{CC3N}	CKE ≥ V _{IH(MIN.)} , t _{CK} = 15 ns, /CS ≥ V _{IH(MIN.)} , Input signals are changed one time during 30 ns.			100	mA	
	I _{CC3NS}	CKE ≥ V _{IH(MIN.)} , t _{CK} = ∞, Input signals are stable.			40		
Operating current (Burst mode)	I _{CC4}	t _{CK} ≥ t _{CK(MIN.)} , I _O = 0 mA	/CAS latency = 2	-A80	660	mA	2
				-A10	520		
			/CAS latency = 3	-A80	780		
				-A10	660		
Refresh current	I _{CC5}		/CAS latency = 2	-A80	520	mA	3
				-A10	520		
			/CAS latency = 3	-A80	540		
				-A10	540		
Self refresh current	I _{CC6}	CKE ≤ 0.2 V			4	mA	
Input leakage current	I _{I(L)}	V _I = 0 to 3.6 V, All other pins not under test = 0 V		-4	+4	μA	
Output leakage current	I _{O(L)}	D _{OUT} is disabled, V _O = 0 to 3.6 V		-1.5	+1.5	μA	
★ High level output voltage	V _{OH}	I _O = -4.0 mA		2.4		V	
★ Low level output voltage	V _{OL}	I _O = +4.0 mA			0.4	V	

- Notes**
1. I_{CC1} depends on output loading and cycle rates. Specified values are obtained with the output open. In addition to this, I_{CC1} is measured on condition that addresses are changed only one time during t_{CK(MIN.)}.
 2. I_{CC4} depends on output loading and cycle rates. Specified values are obtained with the output open. In addition to this, I_{CC4} is measured on condition that addresses are changed only one time during t_{CK(MIN.)}.
 3. I_{CC5} is measured on condition that addresses are changed only one time during t_{CK(MIN.)}.

AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

AC Characteristics Test Conditions

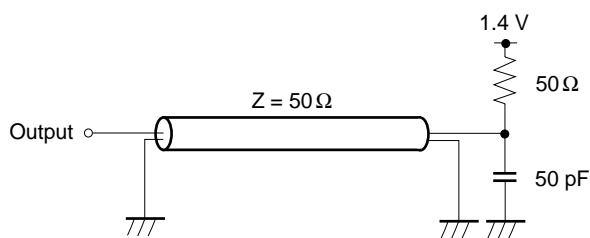
- AC measurements assume $t_r = 1$ ns.
- Reference level for measuring timing of input signals is 1.4 V. Transition times are measured between V_{IH} and V_{IL} .
- If t_r is longer than 1 ns, reference level for measuring timing of input signals is $V_{IH(MIN.)}$ and $V_{IL(MAX.)}$.
- An access time is measured at 1.4 V.



Synchronous Characteristics

Parameter		Symbol	-A80		-A10		Unit	Note
			MIN.	MAX.	MIN.	MAX.		
Clock cycle time	/CAS latency = 3	t _{CK3}	8	(125 MHz)	10	(100 MHz)	ns	
	/CAS latency = 2	t _{CK2}	10	(100 MHz)	13	(77 MHz)	ns	
Access time from CLK	/CAS latency = 3	t _{AC3}		6		6	ns	1
	/CAS latency = 2	t _{AC2}		6		7	ns	1
CLK high level width		t _{CH}	3		3		ns	
CLK low level width		t _{CL}	3		3		ns	
Data-out hold time		t _{OH}	3		3		ns	1
Data-out low-impedance time		t _{LZ}	0		0		ns	
Data-out high-impedance time	/CAS latency = 3	t _{HZ3}	3	6	3	6	ns	
	/CAS latency = 2	t _{HZ2}	3	6	3	7	ns	
Data-in setup time		t _{DS}	2		2		ns	
Data-in hold time		t _{DH}	1		1		ns	
Address setup time		t _{AS}	2		2		ns	
Address hold time		t _{AH}	1		1		ns	
CKE setup time		t _{CKS}	2		2		ns	
CKE hold time		t _{CKH}	1		1		ns	
CKE setup time (Power down exit)		t _{CKSP}	2		2		ns	
Command (/CS0, /CS2, /RAS, /CAS, /WE, DQMB0 - DQMB7) setup time		t _{CMS}	2		2		ns	
Command (/CS0, /CS2, /RAS, /CAS, /WE, DQMB0 - DQMB7) hold time		t _{CMH}	1		1		ns	

Note 1. Output load



★ Remark These specifications are applied to the monolithic device.

Asynchronous Characteristics

Parameter	Symbol	-A80		-A10		Unit	Note
		MIN.	MAX.	MIN.	MAX.		
REF to REF/ACT command period	t _{RC}	70		70		ns	
ACT to PRE command period	t _{RAS}	48	120,000	50	120,000	ns	
PRE to ACT command period	t _{RP}	20		20		ns	
Delay time ACT to READ/WRITE command	t _{RCD}	20		20		ns	
ACT (0) to ACT (1) command period	t _{RRD}	16		20		ns	
Data-in to PRE command period	t _{DPL}	8		10		ns	
Data-in to ACT (REF) command period (Auto precharge)	/CAS latency = 3	t _{DAL3}	1CLK+20		1CLK+20	ns	
	/CAS latency = 2	t _{DAL2}	1CLK+20		1CLK+20	ns	
Mode register set cycle time	t _{RSC}	2		2		CLK	
Transition time	t _T	0.5	30	1	30	ns	
Refresh time	t _{REF}		64		64	ms	

Serial PD

(1/2)

Byte No.	Function Described	Hex	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Notes	
0	Defines the number of bytes written into serial PD memory	80H	1	0	0	0	0	0	0	0	128 bytes	
1	Total number of bytes of serial PD memory	08H	0	0	0	0	1	0	0	0	256 bytes	
2	Fundamental memory type	04H	0	0	0	0	0	1	0	0	SDRAM	
3	Number of rows	0CH	0	0	0	0	1	1	0	0	12 rows	
4	Number of columns	08H	0	0	0	0	1	0	0	0	8 columns	
5	Number of banks	01H	0	0	0	0	0	0	0	1	1 bank	
6	Data width	40H	0	1	0	0	0	0	0	0	64 bits	
7	Data width (continued)	00H	0	0	0	0	0	0	0	0	0	
8	Voltage interface	01H	0	0	0	0	0	0	0	1	LVTTTL	
9	CL = 3 cycle time	-A80	80H	1	0	0	0	0	0	0	0	8 ns
		-A10	A0H	1	0	1	0	0	0	0	0	10 ns
10	CL = 3 access time	-A80	60H	0	1	1	0	0	0	0	0	6 ns
		-A10	60H	0	1	1	0	0	0	0	0	6 ns
11	DIMM configuration type	00H	0	0	0	0	0	0	0	0	None	
12	Refresh rate / type	80H	1	0	0	0	0	0	0	0	Normal	
13	SDRAM width	10H	0	0	0	1	0	0	0	0	x16	
14	Error checking SDRAM width	00H	0	0	0	0	0	0	0	0	None	
15	Minimum clock delay	01H	0	0	0	0	0	0	0	1	1 clock	
16	Burst length supported	8FH	1	0	0	0	1	1	1	1	1, 2, 4, 8, F	
17	Number of banks on each SDRAM	04H	0	0	0	0	0	1	0	0	4 banks	
18	/CAS latency supported	06H	0	0	0	0	0	1	1	0	2, 3	
19	/CS latency supported	01H	0	0	0	0	0	0	0	1	0	
20	/WE latency supported	01H	0	0	0	0	0	0	0	1	0	
21	SDRAM module attributes	00H	0	0	0	0	0	0	0	0		
22	SDRAM device attributes : General	0EH	0	0	0	0	1	1	1	0		
23	CL = 2 cycle time	-A80	A0H	1	0	1	0	0	0	0	0	10 ns
		-A10	D0H	1	1	0	1	0	0	0	0	13 ns
24	CL = 2 access time	-A80	60H	0	1	1	0	0	0	0	0	6 ns
		-A10	70H	0	1	1	1	0	0	0	0	7 ns
25-26		00H	0	0	0	0	0	0	0	0		
27	t _{RP} (MIN.)	-A80	14H	0	0	0	1	0	1	0	0	20 ns
		-A10	14H	0	0	0	1	0	1	0	0	20 ns
28	t _{RRD} (MIN.)	-A80	10H	0	0	0	1	0	0	0	0	10 ns
		-A10	14H	0	0	0	1	0	1	0	0	20 ns
29	t _{RCD} (MIN.)	-A80	14H	0	0	0	1	0	1	0	0	20 ns
		-A10	14H	0	0	0	1	0	1	0	0	20 ns
30	t _{RAS} (MIN.)	-A80	30H	0	0	1	1	0	0	0	0	48 ns
		-A10	32H	0	0	1	1	0	0	1	0	50 ns
31	Module bank density	08H	0	0	0	0	1	0	0	0	32 bytes	

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(2/2)

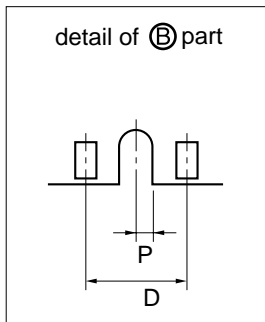
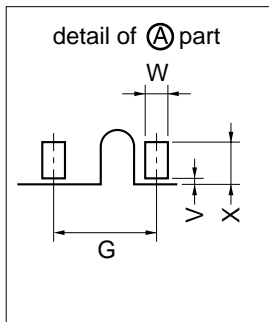
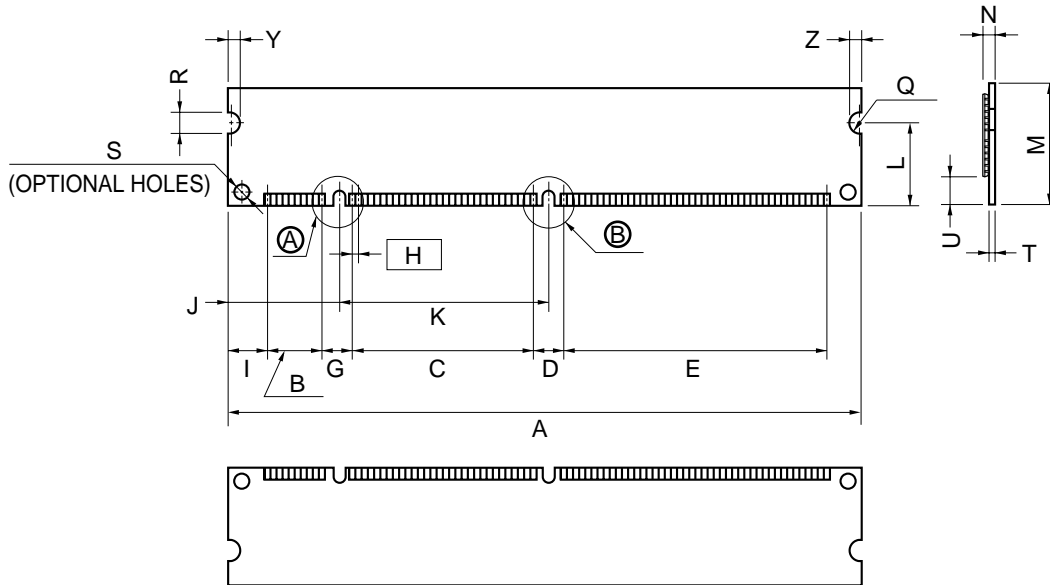
Byte No.	Function Described	Hex	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Notes	
32	Command and address signal input setup time	20H	0	0	1	0	0	0	0	0	2 ns	
33	Command and address signal input hold time	10H	0	0	0	1	0	0	0	0	1 ns	
34	Data signal input setup time	20H	0	0	1	0	0	0	0	0	2 ns	
35	Data signal input hold time	10H	0	0	0	1	0	0	0	0	1 ns	
36-61		00H	0	0	0	0	0	0	0	0		
62	SPD revision	12H	0	0	0	1	0	0	1	0	1.2	
★ ★	63 Checksum for bytes 0 - 62	-A80	DEH	1	1	0	1	1	1	1	0	
		-A10	44H	0	1	0	0	0	1	0	0	
64-71	Manufacture's JEDEC ID code											
72	Manufacturing location											
73-90	Manufacture's P/N											
91-92	Revision code											
93-94	Manufacturing date											
95-98	Assembly serial number											
99-125	Mfg specific											
126	Intel specification frequency	64H	0	1	1	0	0	1	0	0	100 MHz	
127	Intel specification /CAS	-A80	A7H	1	0	1	0	0	1	1	1	
	latency support	-A10	A5H	1	0	1	0	0	1	0	1	

Timing Chart

Please refer to NEC Synchronous DRAM Data sheet.

★ Package Drawing

168 PIN DUAL IN-LINE MODULE (SOCKET TYPE)



ITEM	MILLIMETERS	INCHES
A	133.35±0.13	5.250±0.006
B	11.43	0.450
C	36.83	1.450
D	6.35	0.250
E	54.61	2.150
G	6.35	0.250
H	1.27 (T.P.)	0.050 (T.P.)
I	8.89	0.350
J	24.495	0.964
K	42.18	1.661
L	17.78	0.700
M	34.93	1.375
N	4.0 MAX.	0.158 MAX.
P	1.0	0.039
Q	R2.0	R0.079
R	4.0±0.1	0.157 ^{+0.005} _{-0.004}
S	φ3.0	φ0.118
T	1.27±0.1	0.05±0.004
U	4.0 MIN.	0.157 MIN.
V	0.2±0.15	0.00787 ±0.0059
W	1.0±0.05	0.039 ^{+0.003} _{-0.002}
X	2.54 MIN.	0.100±0.004
Y	3.0 MIN.	0.118 MIN.
Z	3.0 MIN.	0.118 MIN.

[MEMO]

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

[MEMO]

CAUTION FOR HANDLING MEMORY MODULES

When handling or inserting memory modules, be sure not to touch any components on the modules, such as the memory IC, chip capacitors and chip resistors. It is necessary to avoid undue mechanical stress on these components to prevent damaging them.

When re-packing memory modules, be sure the modules are NOT touching each other. Modules in contact with other modules may cause excessive mechanical stress, which may damage the modules.

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NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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Anti-radioactive design is not implemented in this product.